INTERNATIONAL SEARCH REPORT

International application No.
PCT/JP2005/012886

_	CATION OF SUBJECT MATTER 7 C30B29/38, 19/02, 19/04					
According to International Patent Classification (IPC) or to both national classification and IPC						
B. FIELDS SE	EARCHED		•			
	nentation searched (classification system followed by cl C30B29/38, 19/02, 19/04	assification symbols)	·			
Jitsuyo Kokai Ji Electronic data b		tsuyo Shinan Toroku Koho oroku Jitsuyo Shinan Koho	1996-2005 1994-2005			
C DOCUMEN	NTS CONSIDERED TO BE RELEVANT					
	•		<u>T </u>			
Category*	Citation of document, with indication, where appropriate, of the relevant passages		Relevant to claim No.			
X A	Masato AOKI et al., Condition		5,6			
A	growth of GaN crystals by the method, Materials Letters, 20		1-4			
	pages 660 to 664	•				
X .	TD 2004 100540 3 (G	ishol Minimo Co				
A	JP 2004-189549 A (Sumitomo M Ltd.),	letar mining Co.,	5,6 1-4			
	08 July, 2004 (08.07.04),					
	Claims 1, 4; Par. Nos. [0046]	to [0051];				
	example 1 (Family: none)		. ,			
	· · · · · · · · · · · · · · · · · · ·					
A	WO 2002/099169 A1 (The New I	ndustry Research	1-6			
Ź	Organization), 12 December, 2002 (12.12.02),					
	Claims 4, 5; page 5, lines 7 to 25					
	& EP 1403404 A1 & US					
× Further do	cuments are listed in the continuation of Box C.	See patent family annex.				
* Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "T" later document published after the international filing date or placed to understant the principle or theory underlying the invention						
to be of particular relevance "E" earlier application or patent but published on or after the international		"X" document of particular relevance; the c	laimed invention cannot be			
filing date "L" document w	hich may throw doubts on priority claim(s) or which is	considered novel or cannot be consisted when the document is taken alone				
cited to establish the publication date of another citation or other special reason (as specified)		"Y" document of particular relevance; the c				
"O" document referring to an oral disclosure, use, exhibition or other means		considered to involve an inventive combined with one or more other such	documents, such combination			
	sument published prior to the international filing date but later than priority date claimed "&" document member of the same patent family					
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	l completion of the international search ist, 2005 (19.08.05)	Date of mailing of the international sear 06 September, 2005	_			
Name and mailing	mailing address of the ISA/ Authorized officer					
Japanese Patent Office		·				
Facsimile No.		Telephone No.				

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PCT/JP2005/012886

Citegory* Citation of document, with indication, where appropriate, of the relevant passages Rolevant to claim N A Hisanori YAMANE et al., "Flux-ho ni yoru 1-6 Gan Tankeesho no Ikusei", Oyo Butsuri, 2002, Vol.71, No.5, pages 548 to 552 P.A JF 2004-277224 A (Ricoh Co., Ltd.), 07 October, 2004 (07.10.04) & US 2004/0226503 Al P.A S. DHAR et al., Observation of a 0.7 eV electron trap in dilute GaAsN layers grown by liquid phase epitaxy, Applied Physics Letters, 09 August, 2004 (09.08.04), Vol.85, No.6, pages 964 to 966 Citation of devent passages Rolevant to claim N 1-6 1-6 1-7 1-7 1-7 1-8 1-9 1-9 1-9 1-9 1-9 1-9 1-9 1-10 1-1		DOCUMENTS CONSIDERED TO BE RELEVANT	1	
GaN Tankessho no Ikusei", Oyo Butsuri, 2002, Vol.71, No.5, pages 548 to 552 P,A JP 2004-277224 A (Ricoh Co., Ltd.), 07 October, 2004 (07.10.04) & US 2004/0226503 A1 P,A S. DHAR et al., Observation of a 0.7 eV electron trap in dilute GaAsN layers grown by liquid phase epitaxy, Applied Physics Letters, 09 August, 2004 (09.08.04), Vol.85,	Category*		Relevant to claim No.	
07 October, 2004 (07.10.04) & US 2004/0226503 A1 P,A S. DHAR et al., Observation of a 0.7 eV electron trap in dilute GaAsN layers grown by liquid phase epitaxy, Applied Physics Letters, 09 August, 2004 (09.08.04), Vol.85,	A	GaN Tankessho no Ikusei", Oyo Butsuri,	1-6	
electron trap in dilute GaAsN layers grown by liquid phase epitaxy, Applied Physics Letters, 09 August, 2004 (09.08.04), Vol.85,	P,A	07 October, 2004 (07.10.04)	1-6	
	P,A	electron trap in dilute GaAsN layers grown by liquid phase epitaxy, Applied Physics Letters, 09 August, 2004 (09.08.04), Vol.85,	·	1-6
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